

150V N-Channel Power MOSFET

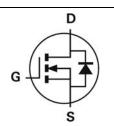
 $V_{\text{DSS}}$  , 150V

 $R_{\text{DS(ON)}}$  ,  $39m\Omega$  (max.) @ VGs=10V

 $I_D$  , 32A







Description	Features
The SG150N05D uses advanced Trench technology and designs to provide excellent R <sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input/Output Leakage</li> <li>Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul> <li>Motor / Body Load Control</li> <li>Automotive Systems</li> <li>Solenoid and Motor Control</li> <li>DC-DC converters and Off-line UPS</li> </ul>

**Ordering Information** 

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG150N05D	Halogen-Free	TO-252	D	Tape & Reel	2,500

Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parame	ter	Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	150	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current Centinuous	Tc=25°C	I-	32	Α
Drain Current-Continuous	T <sub>C</sub> =75°C	I <sub>D</sub>	25	А
Drain Current-Pulsed Note 1		I <sub>DM</sub>	75	Α
Desir Comment Continuous	T <sub>A</sub> =25°C		5.6	А
Drain Current-Continuous	T <sub>A</sub> =75°C	I <sub>D</sub>	4.3	А
Avalanche Current, L=1mH, V <sub>G</sub> =10V, Rate	ed V <sub>DS</sub> =150V	las	6	А
Avalanche Energy, L=1mH, V <sub>G</sub> =10V, Rate	ed V <sub>DS</sub> =150V	Eas	18	mJ
	Tc=25°C		83	W
Mayimum Dayyar Dissination	T <sub>C</sub> =75°C		50	W
Maximum Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	2.5	W
	T <sub>A</sub> =75°C		1.5	W
Storage Temperature Range		T <sub>STG</sub>	-55 to +175	°C
Operating Junction Temperature Range		TJ	-55 to +175	°C

**Thermal Resistance Ratings** 

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	RθJA	Steady State	-	-	50	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	1.5	°C/W

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#### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =120V, V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	$V_{GS}=\pm30V$ , $V_{DS}=0V$	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA	2	3	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>DS</sub> =15A	-	-	39	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	1933	-	
Output Capacitance	Coss	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	-	147	-	pF
Reverse Transfer Capacitance	Crss		=	49	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$		-	22	-	
Rise Time	tr	V <sub>DS</sub> =75V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V,	-	10	-	]
Turn-Off Delay Time	T <sub>d(off)</sub>	R <sub>GEN</sub> =3Ω	-	12	-	ns
Fall Time	tf		-	35	-	]
Total Gate Charge at 10V	Qg		-	55	-	
Gate to Source Gate Charge	Q <sub>gs</sub>	V <sub>DS</sub> =75V, I <sub>DS</sub> =20A, V <sub>GS</sub> =10V	-	18	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$		-	17	-	]

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =20A	-	-	1.3	V
Body Diode Reverse Recovery Time	trr	L-15A dl/dt-100A/up	-	25	-	ns
Body Diode Reverse Recovery Charge	Qrr	I <sub>F</sub> =15A, dl/dt=100A/μs	-	32	-	nC

#### Notes:

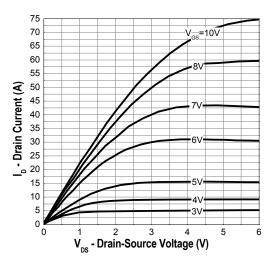
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design. R<sub>BJA</sub> shown below for single device operation on FR-4 in still air.



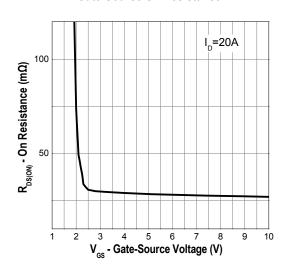
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#### **Typical Operating Characteristics**

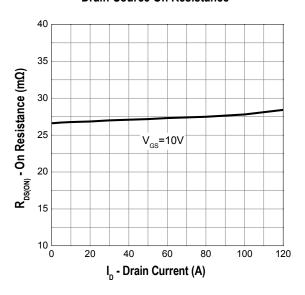
#### **Output Characteristics**



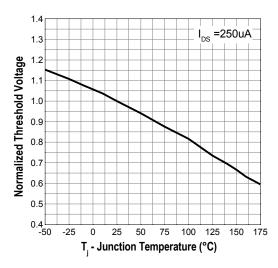
#### **Gate-Source On Resistance**



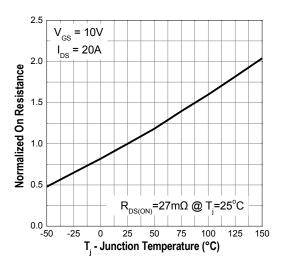
**Drain-Source On Resistance** 



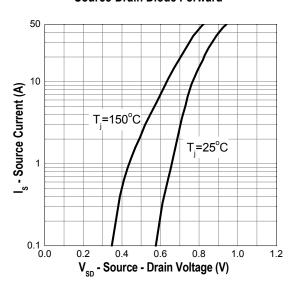
#### **Gate Threshold Voltage**



**Drain-Source On Resistance** 



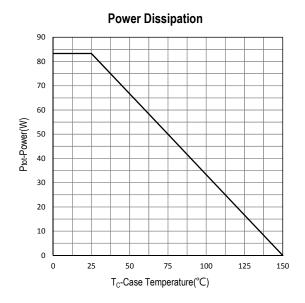
#### Source-Drain Diode Forward



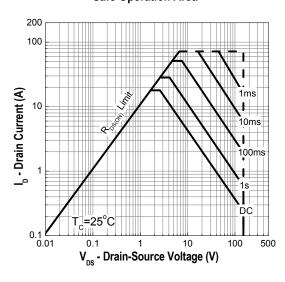


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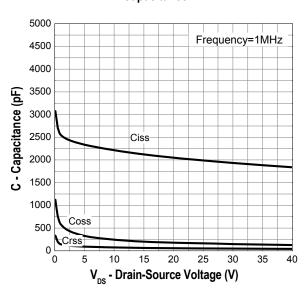
#### **Typical Operating Characteristics (Cont.)**



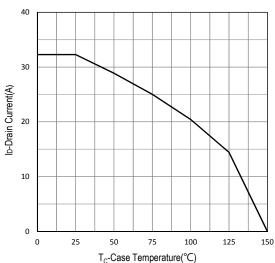
### Safe Operation Area



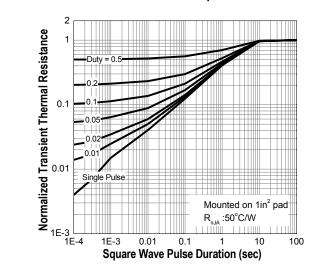
#### Capacitance



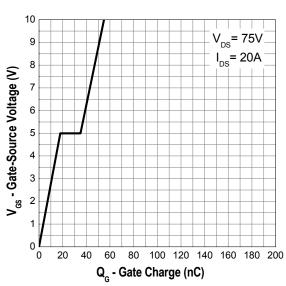
#### **Drain Current**



#### **Transient Thermal Impedance**



#### **Gate Charge**





# SG150N05D 150V N-Channel Power MOSFET

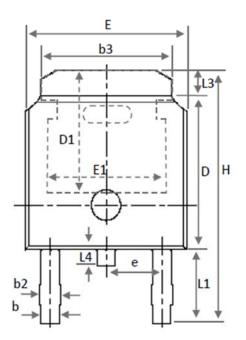
### **Marking Information**

TO-252 (D)	Marking Rule
TO-252 (D)  Laser Marking  SG150N05D  YYMMXXX	Marking Rule  Line 1: Device SG150N05D  Line 2: Date Code YYMMXXX  YY: Year Code MM: Month Code XXX: Serial Number
Diagram	



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### **Package of Dimension**





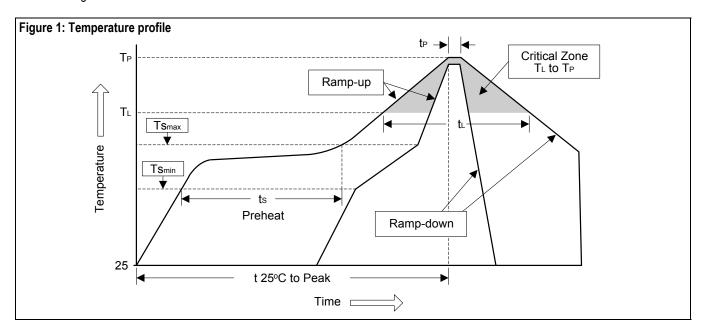
Symbol	Min	Nor	Max
E	6.35	6.54	6.731
L	1.40	1.59	1.78
L1		2.743 Ref	
L2		0.508 BSC	2
L3	0.89	1.08	1.27
L4	0.60	0.81	1.01
D	5.97	6.10	6.223
Н	9.40	9.91	10.41
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	4.95	5.21	5.46
е		2.286 BSC	Ĵ.
Α	2.18	2.29	2.39
A1	0.00	0.07	0.13
c2	0.46	0.68	0.89
D1	5.21	-	-
E1	4.32	-	-



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# **Soldering Methods for Silicongear's Products**1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%

- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 20 ooo	20 to 40 cos
Temperature (t <sub>P</sub> )	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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### **Important Notice**

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